



Sheet 1 of 5

Form 1449*

Atty. Docket No.: 303.557US1

Serial No. 09/259,849

INFORMATION DISCLOSURE STATEMENT
BY APPLICANT

Applicant: Paul A. Farrar

(Use several sheets if necessary)

Filing Date: March 1, 1999

Group: 1765

U.S. PATENT DOCUMENTS

Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
<i>JP</i>	2,842,438	07/08/1958	Saarivirta, et al.	75	135	08/02/56
<i>JP</i>	3,954,570	06/04/1976	Shirk, et al.	201	15	11/11/74
<i>JP</i>	4,386,116	05/31/1983	Nair, et al.	427	99	12/24/81
<i>JP</i>	4,423,547	01/03/1984	Farrar, P.A., et al.	29	571	06/01/81
<i>JP</i>	4,574,095	03/04/1986	Baum, et al.	427	53.1	11/19/84
<i>JP</i>	4,788,082	11/29/1988	Schmitt	427	248.1	12/12/85
<i>JP</i>	4,931,410	06/05/1990	Tokunaga, et al.	437	189	08/25/88
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<i>JP</i>	4,996,584	02/26/1991	Young, P.L., et al.	357	71	10/13/88
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<i>JP</i>	5,158,986	10/27/1992	Cha, et al.	521	82	04/05/91
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Date Considered

5/30/01

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**Examiner Initial	Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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**Examiner Initial	Document Number	Date	Country	Class	Subclass	Translation Yes No
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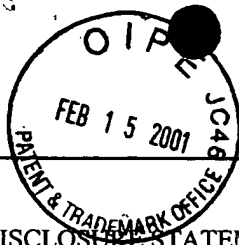
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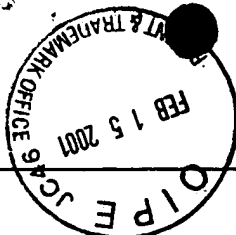
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Guillermo Peralta

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